



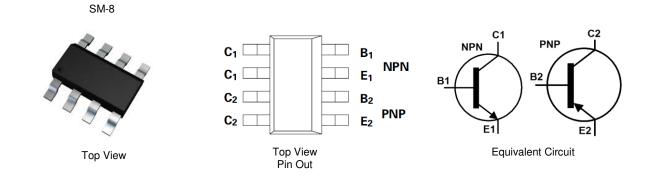
#### COMPLEMENTARY MEDIUM POWER HIGH GAIN TRANSISTOR IN SM-8 PACKAGE

### **Features**

- NPN Transistor
  - BV<sub>CEO</sub> > 45
    - V<sub>CE(sat)</sub> < 100mV @ I<sub>C</sub>= 100mA
  - Continuous Current I<sub>C</sub> = 2A
- PNP Transistor
  - BV<sub>CEO</sub> > -40V
  - V<sub>CE(sat)</sub> < -250mV @ I<sub>C</sub>= -500mA
  - Continuous Current I<sub>C</sub> = -2A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.117 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZDT6790TA	T6790	7	12	1,000
ZDT6790TC	T6790	13	12	4,000

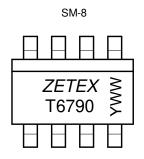
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



T6790 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V <sub>CBO</sub>	45	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	-7	V
Continuous Collector Current	Ic	2	-2	A
Peak Pulse Current (Note 5)	I <sub>CM</sub>	6	-6	A

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Dower Discinction	(Note 5)	D D	2.25	W	
Collector Power Dissipation	(Note 6)	P <sub>D</sub>	2.75	vv	
Thermal Desistance, Junction to Ambient	(Note 5)	D	55.60	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>eja</sub>	45.50	- C/W	
Thermal Resistance, Junction to Leads (Note 7)		R <sub>θJL</sub>	30.68	°C/W	
Operating and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150	°C	

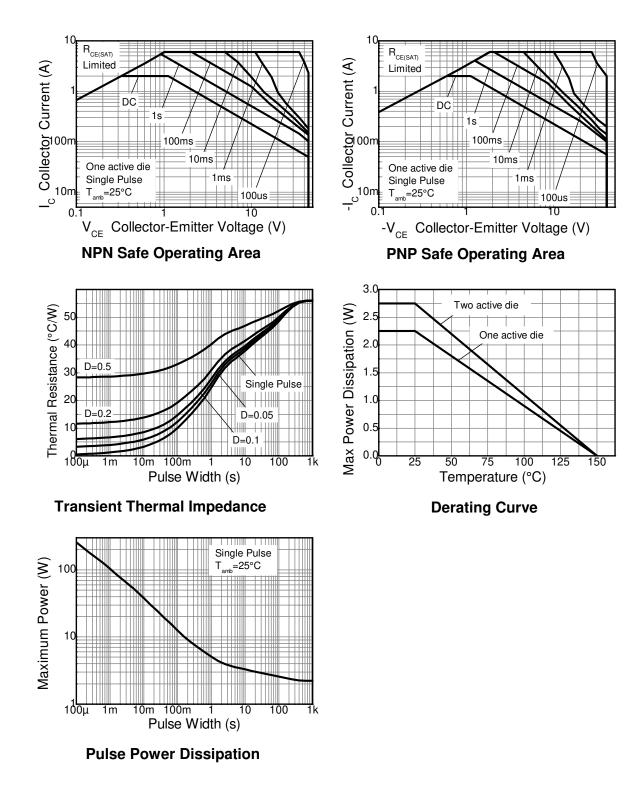
### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

 For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
Same as Note 5, except both die are active and equally sharing power.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:



## **Thermal Characteristics and Derating Information**





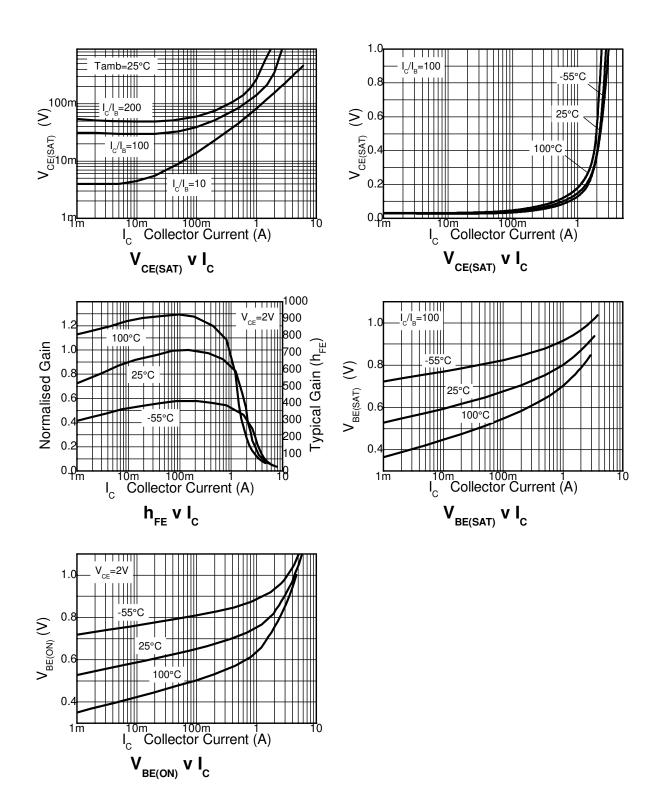
# **NPN - Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	45		_	V	$I_{\rm C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	45	_	_	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	_	—	V	$I_{\rm E} = 100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>		_	100	nA	V <sub>CB</sub> = 35V
Emitter Cut-Off Current	I <sub>EBO</sub>		_	100	nA	$V_{EB} = 6V$
		500	_	_		$I_{C} = 100 \text{mA}, V_{CE} = 2 \text{V}$
DC Current Transfer Static Ratio (Note 9)	h <sub>FE</sub>	400	—	—	—	$I_C = 1A, V_{CE} = 2V$
		150	—	—		$I_C = 2A, V_{CE} = 2V$
Collector Emitter Seturation Valtage (Nate 0)	V <sub>CE(sat)</sub>	_	_	100	mV	$I_{C} = 100 \text{mA}, I_{B} = 0.5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		—	—	500		$I_{C} = 1A, I_{B} = 5mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	_	_	900	mV	$I_{\rm C} = 1$ A, $I_{\rm B} = 10$ mA
Base-Emitter Turn-on Voltage (Note 9)	V <sub>BE(on)</sub>	-	—	900	mV	$I_C = 1A$ , $V_{CE} = 2V$
Transitional Frequency (Note 9)	f <sub>T</sub>	150	-	_	MHz	$I_C = 50mA$ , $V_{CE} = 5V$ , f = 50MHz
Input Capacitance	C <sub>ibo</sub>	_	200	—	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance	C <sub>obo</sub>		16	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Time	ton		33		ns	$V_{CC} = 10V, I_C = 500mA,$
	t <sub>off</sub>		1,300		ns	$I_{B1} = 50mA$ , $I_{B2} = 50mA$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



## **NPN – Typical Electrical Characteristics**





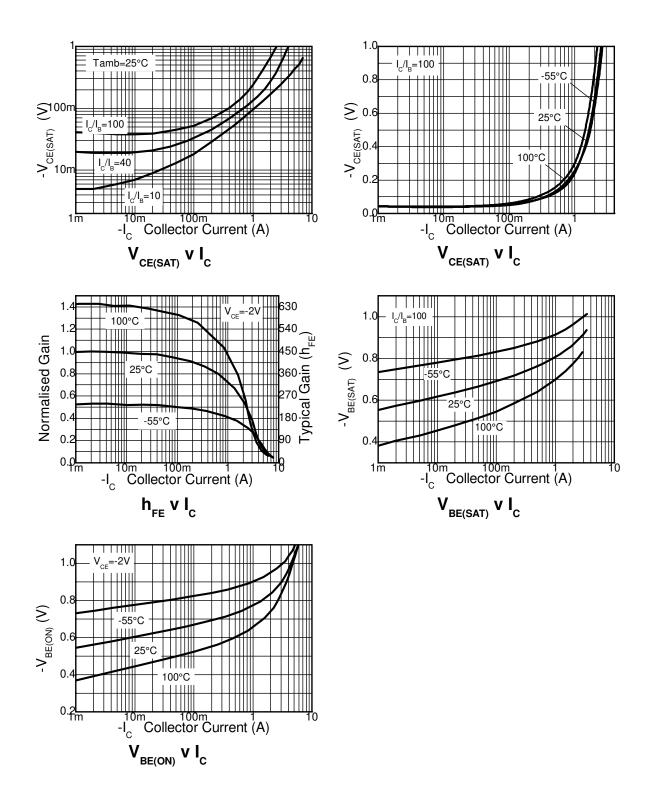
# **PNP - Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

		1	n:			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	<b>BV</b> CBO	-50	—	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-40	_		V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	—	V	I <sub>E</sub> = -100μA
Collector Cut-Off Current	I <sub>CBO</sub>	_	—	-100	nA	V <sub>CB</sub> = -30V
Emitter Cut-Off Current	I <sub>EBO</sub>		_	-100	nA	$V_{EB} = -6V$
		300	_	800		$I_{C} = -10mA, V_{CE} = -2V$
DC Current Transfer Statis Datis (Natas 0)	6	250	_	_		$I_{C} = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Transfer Static Ratio (Notes 9)	h <sub>FE</sub>	200	_	_	_	$I_{\rm C} = -1$ A, $V_{\rm CF} = -2$ V
		150	—	—		$I_{C} = -2A, V_{CE} = -2V$
	V <sub>CE(sat)</sub>		_	-250		I <sub>C</sub> = -500mA, I <sub>B</sub> = -5mA
Collector-Emitter Saturation Voltage (Notes 9)			_	-450	mV	$I_{\rm C} = -1A, I_{\rm B} = -10mA$
			—	-750		$I_{\rm C} = -2A, I_{\rm B} = -50mA$
Base-Emitter Saturation Voltage (Notes 9)	V <sub>BE(sat)</sub>	_	_	-1,000	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA
Base-Emitter Turn-on Voltage (Notes 9)	V <sub>BE(on)</sub>	_	-750	_	mV	$I_{C} = -1A, V_{CE} = -2V$
Transitional Frequency (Notes 9)	fT	100	-	—	MHz	$I_C = -50$ mA, $V_{CE} = -5V$ , f = 50MHz
Input Capacitance	C <sub>ibo</sub>	_	225	_	pF	V <sub>EB</sub> = -0.5V, f = 1MHz,
Output Capacitance	Cobo		24	_	pF	$V_{CB} = -10V, f = 1MHz,$
Switching Time	ton		35		ns	$V_{CC} = -10V, I_{C} = -500mA,$
Switching Time	t <sub>off</sub>		600		ns	$I_{B1} = -50mA, I_{B2} = -50mA$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



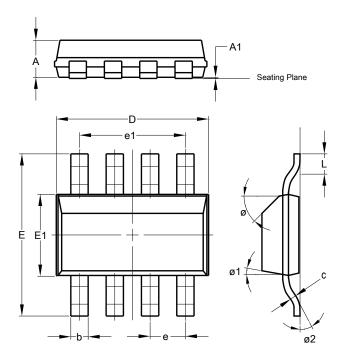
## **PNP – Typical Electrical Characteristics**





## **Package Outline Dimensions**

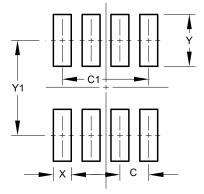
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SM-8					
Dim	Min Max Typ					
Α		1.70	1.60			
A1	0.02	0.10	0.04			
b	0.70	0.90	0.80			
С	0.24	0.32	0.28			
D	6.30	6.30 6.70 6.60				
е	1.53 REF					
e1	4.59 REF					
Е	6.70	7.30	7.00			
E1	3.30	3.70	3.50			
L	0.75	0.75 1.00 0.90				
Ø	45°					
Ø1	-	15°	-			
Ø2	-	-	10°			
All I	All Dimensions in mm					

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.52
C1	4.6
Х	0.95
Y	2.80
Y1	6.80



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